Preferred Device

# Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

PNPN devices designed for high volume, low cost consumer applications such as temperature, light and speed control; process and remote control; and warning systems where reliability of operation is critical.

- Small Size
- Passivated Die Surface for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Recommend Electrical Replacement for C106
- Surface Mount Package Case 369A
- Device Marking: Device Type, e.g., for MCR703A: CR703A, Date Code

#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>C</sub> = -40 to +110°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR703A MCR704A MCR706A MCR708A	Vdrm, Vrrm	100 200 400 600	Volts
$\begin{array}{llllllllllllllllllllllllllllllllllll$	VRSM	150 250 450 650	Volts
On–State RMS Current (180° Conduction Angles, T <sub>C</sub> = 90°C)	<sup>I</sup> T(RMS)	4.0	Amps
Average On–State Current (180° Conduction Angles) $T_C = -40 \text{ to } +90^{\circ}\text{C}$ $T_C = +100^{\circ}\text{C}$	IT(AV)	2.6 1.6	Amps
Non-Repetitive Surge Current (1/2 Sine Wave, 60 Hz, T <sub>J</sub> = 110°C) (1/2 Sine Wave, 1.5 ms, T <sub>J</sub> = 110°C)	ITSM	25 35	Amps
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	2.6	A <sup>2</sup> s
Forward Peak Gate Power (Pulse Width $\leq$ 10 $\mu$ s, T <sub>C</sub> = 90°C)	PGM	0.5	Watt
Forward Average Gate Power (t = 8.3 ms, $T_C$ = 90°C)	PG(AV)	0.1	Watt
Forward Peak Gate Current (Pulse Width $\leq$ 10 $\mu$ s, T <sub>C</sub> = 90°C)	IGM	0.2	Amp
Operating Junction Temperature Range	Тј	-40 to +110	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

(1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

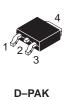


### **ON Semiconductor**

http://onsemi.com

# SCRs 4.0 AMPERES RMS 100 thru 600 VOLTS





CASE 369A STYLE 5

PIN ASSIGNMENT				
1 Gate				
2	Anode			
3	Cathode			
4	Anode			

#### **ORDERING INFORMATION**

Device	Package	Shipping		
MCR703AT4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)		
MCR704AT4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)		
MCR706AT4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)		
MCR708AT4	DPAK 369A	16mm Tape and Reel (2.5K/Reel)		

**Preferred** devices are recommended choices for future use and best overall value.

### THERMAL CHARACTERISTICS

Characteristic			Symbol	№	Max	
Thermal Resistance, Junction to Case			R <sub>θJC</sub>	8	8.33	
Thermal Resistance, Junction to Ambient <sup>(1)</sup>			$R_{\theta JA}$	1	80	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds		) Seconds	ΤL	2	260	
ELECTRICAL CHARACTERISTICS (T <sub>C</sub> = 25°C	unless otherwise not	ted.)				
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•		•	
Peak Repetitive Forward or Reverse Blocking Curren ( $V_{AK}$ = Rated $V_{DRM}$ or $V_{RRM}$ ; $R_{GK}$ = 1 K $\Omega$ )	nt T <sub>C</sub> = 25°C T <sub>C</sub> = 110°C	IDRM, IRR	M		10 200	μA
ON CHARACTERISTICS			•			
Peak Forward "On" Voltage (I <sub>TM</sub> = 8.2 A Peak, Pulse Width = 1 to 2 ms, 2% D	outy Cycle)	V <sub>TM</sub>	_	-	2.2	Volts
Gate Trigger Current (Continuous dc) <sup>(2)</sup> (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 24 Ohms)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	IGT		25 —	75 300	μA
Gate Trigger Voltage (Continuous dc) <sup>(2)</sup> (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 24 Ohms)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$	VGT		_	0.8 1.0	Volts
Gate Non-Trigger Voltage <sup>(2)</sup> (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>C</sub> = 110°C)		V <sub>GD</sub>	0.2	-	-	Volts
Holding Current (V <sub>AK</sub> = 12 Vdc, Gate Open) (Initiating Current = 200 mA)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	Ч		_	5.0 10	mA
Peak Reverse Gate Blocking Voltage $(I_{GR} = 10 \ \mu A)$		VRGM	10	12.5	18	Volts
Peak Reverse Gate Blocking Current (V <sub>GR</sub> = 10 V)		IRGM	_	-	1.2	μΑ
Total Turn-On Time (Source Voltage = 12 V, $R_S = 6 \text{ k Ohms}$ ) ( $I_{TM} = 8.2 \text{ A}$ , $I_{GT} = 2 \text{ mA}$ , Rated $V_{DRM}$ ) (Rise Time = 20 ns, Pulse Width = 10 $\mu$ s)		tgt	-	2.0	-	μs
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM}, R_{GK} = 1 K\Omega, Exponential Wa T_C = 110°C)$	aveform,	dv/dt	-	10	-	V/µs
Repetitive Critical Rate of Rise of On–State Current		di/dt	-	-	100	A/μs

(Cf = 60 Hz,  $I_{PK}$  = 30 A, PW = 100 µs, diG/dt = 1 A/µs)

(1) Case 369A when surface mounted on minimum pad sizes recommended.

(2) R<sub>GK</sub> current not included in measurement.

# Voltage Current Characteristic of SCR

		+ Current Anode +
Symbol	Parameter	T /← ∨ <sub>TM</sub>
VDRM	Peak Repetitive Off State Forward Voltage	
	Peak Forward Blocking Current	on state
VRRM	Peak Repetitive Off State Reverse Voltage	I <sub>RRM</sub> at V <sub>RRM</sub>
IRRM	Peak Reverse Blocking Current	
VTM	Peak On State Voltage	+ Voltage
Ι <sub>Η</sub>	Holding Current	Reverse Blocking Region
		(off state)     Forward Blocking Region       Reverse Avalanche Region     (off state)       Anode –
110		S 5.0 30°C
105	30°C 90°C 90°C 120°C 180°C	DULT SSS 3.0 00°C 120°C 120°C
105 100 95 0		
0	1.0 2.0 3.0 4.0	5.0 0 1.0 2.0 3.0 4.0 5.0
	I <sub>T(AV)</sub> , AVERAGE ON–STATE CURRENT (AMPS) Figure 1. Average Current Derating	I <sub>T(AV)</sub> , AVERAGE ON-STATE CURRENT (AMPS) Figure 2. On–State Power Dissipation
100 Туріса	al @ T <sub>J</sub> = 25°C	
10	Maximum @ T J = 110°C	$Z_{\Theta JC(t)} = R_{\Theta JC(t)} \bullet r(t)$
1.0	Maximum @ T」 = 25°C	$\hat{U}_{i}$
0.1	1.0 1.5 2.0 2.5 3.0 3.5 4.0	
		4.5 0.1 1.0 10 100 1000 10,000 t, TIME (ms)
V	V <sub>T</sub> , INSTANTANEOUS ON–STATE VOLTAGE (VOLTS)	
	Figure 3. On–State Characteristics	Figure 4. Transient Thermal Response

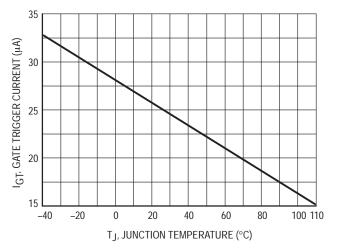


Figure 5. Typical Gate Trigger Current versus Junction Temperature

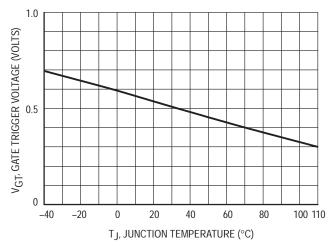


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

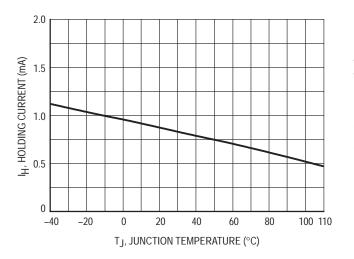


Figure 7. Typical Holding Current versus Junction Temperature

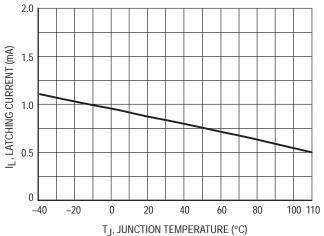
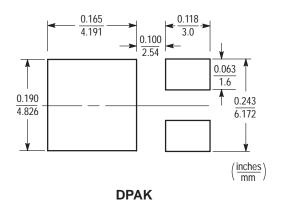


Figure 8. Typical Latching Current versus Junction Temperature

## MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

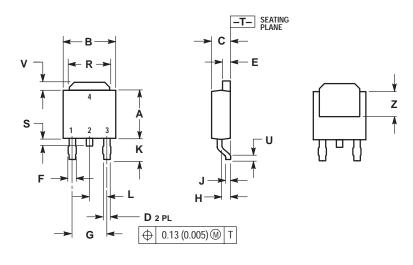
Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



## PACKAGE DIMENSIONS





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
К	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020		0.51	
٧	0.030	0.050	0.77	1.27
Ζ	0.138		3.51	

STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE

# **Notes**

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